

Single P-channel MOSFET

ELM34407AA-N

■ General description

ELM34407AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

■ Features

- $V_{ds} = -30V$
- $I_d = -8A$
- $R_{ds(on)} < 32m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} < 55m\Omega$ ($V_{gs} = -4.5V$)

■ Maximum absolute ratings

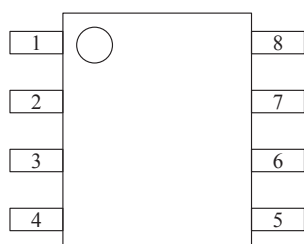
Parameter	Symbol	Limit	Unit	Note
Drain-source voltage	V_{ds}	-30	V	
Gate-source voltage	V_{gs}	± 25	V	
Continuous drain current	I_d	$T_a = 25^\circ C$	-8	A
		$T_a = 70^\circ C$	-7	
Pulsed drain current	I_{dm}	-30	A	3
Power dissipation	P_d	$T_a = 25^\circ C$	2.5	W
		$T_a = 70^\circ C$	1.3	
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$	

■ Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-case	Steady-state	$R\theta_{jc}$		25	$^\circ C/W$	
Maximum junction-to-ambient	Steady-state	$R\theta_{ja}$		50	$^\circ C/W$	

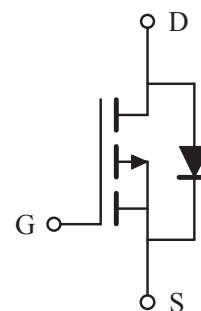
■ Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■ Circuit



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■Electrical characteristics

Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BVdss	Id=-250μA, Vgs=0V	-30			V	
Zero gate voltage drain current	Idss	Vds=-24V, Vgs=0V			-1	μA	
		Vds=-20V, Vgs=0V, Tj=125°C			-10		
Gate-body leakage current	Igss	Vds=0V, Vgs=±25V			±100	nA	
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=-250μA	-0.8	-1.5	-2.5	V	
On state drain current	Id(on)	Vgs=-10V, Vds=-5V	-30			A	1
Static drain-source on-resistance	Rds(on)	Vgs=-10V, Id=-8A		26	32	mΩ	1
		Vgs=-4.5V, Id=-6A		44	55	mΩ	
Forward transconductance	Gfs	Vds=-10V, Id=-6A		7		S	1
Diode forward voltage	Vsd	Is=-1A, Vgs=0V			-1	V	1
Max. body-diode continuous current	Is				-3	A	
Pulsed body-diode current	Ism				-6	A	3
DYNAMIC PARAMETERS							
Input capacitance	Ciss			920		pF	
Output capacitance	Coss	Vgs=0V, Vds=-15V, f=1MHz		190		pF	
Reverse transfer capacitance	Crss			120		pF	
SWITCHING PARAMETERS							
Total gate charge	Qg	Vgs=-10V, Vds=-15V Id=-6A		18.5		nC	2
Gate-source charge	Qgs			2.7		nC	2
Gate-drain charge	Qgd			4.5		nC	2
Turn-on delay time	td(on)	Vgs=-10V, Vds=-10V Id≈-1A, Rgen=3Ω		7.7		ns	2
Turn-on rise time	tr			5.7		ns	2
Turn-off delay time	td(off)			20.0		ns	2
Turn-off fall time	tf			9.5		ns	2
Body diode reverse recovery charge	Qrr			7.9		nC	

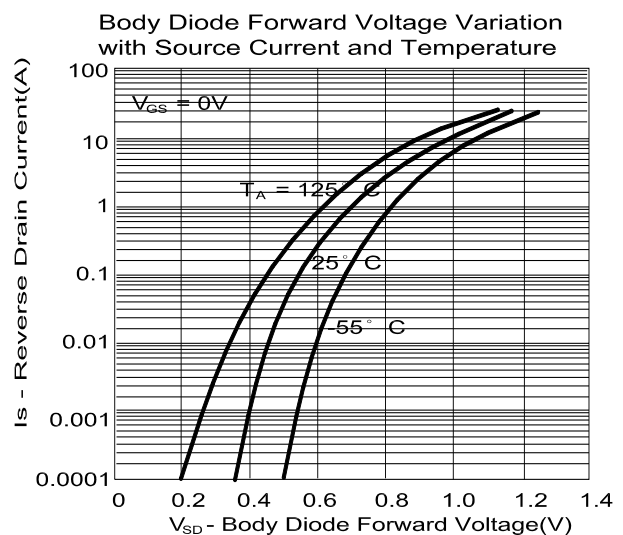
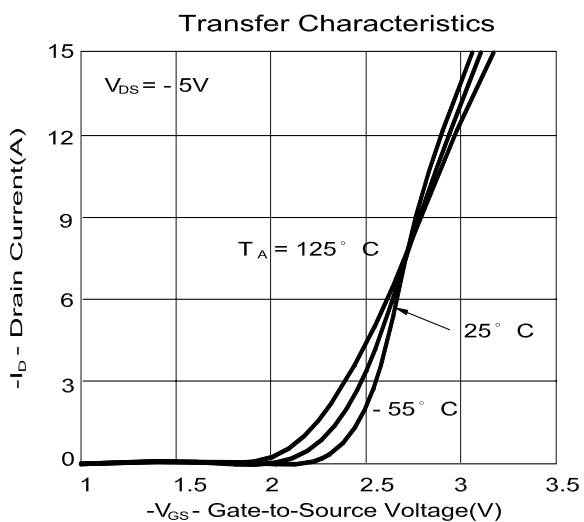
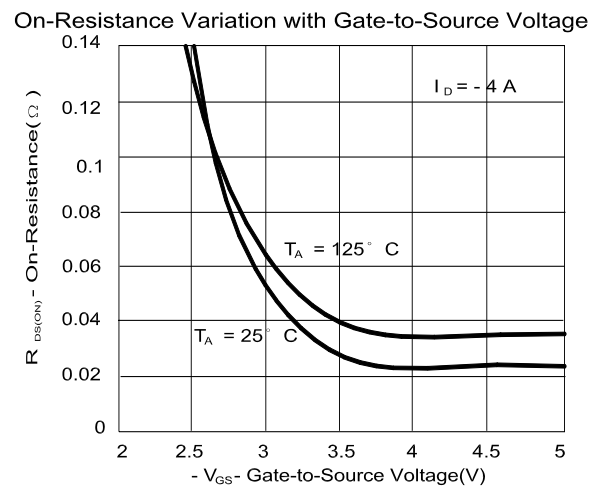
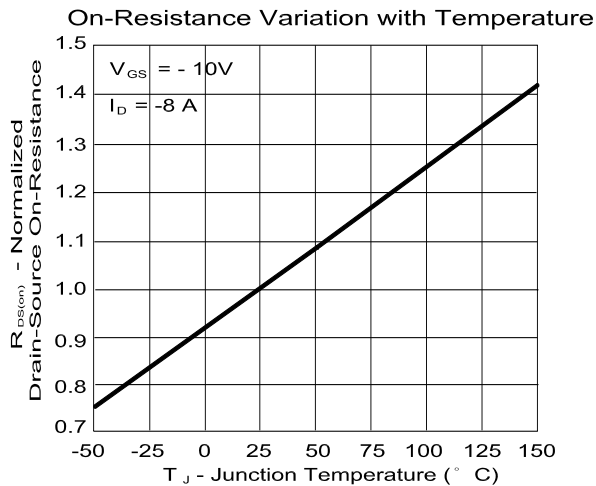
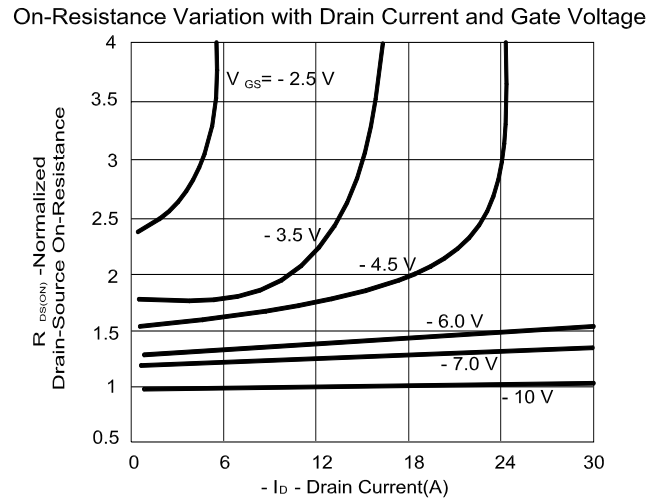
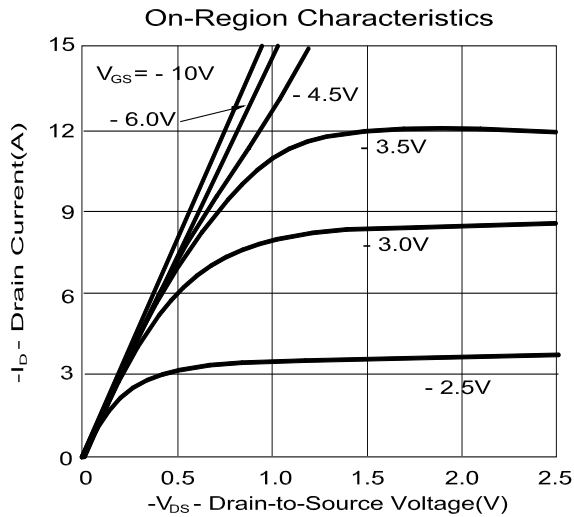
NOTE :

1. Pulsed width ≤ 300μsec and Duty cycle ≤ 2%.
2. Independent of operating temperature.
3. Pulsed width limited by maximum junction temperature.
4. Duty cycle ≤ 1%.

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Typical electrical and thermal characteristics



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